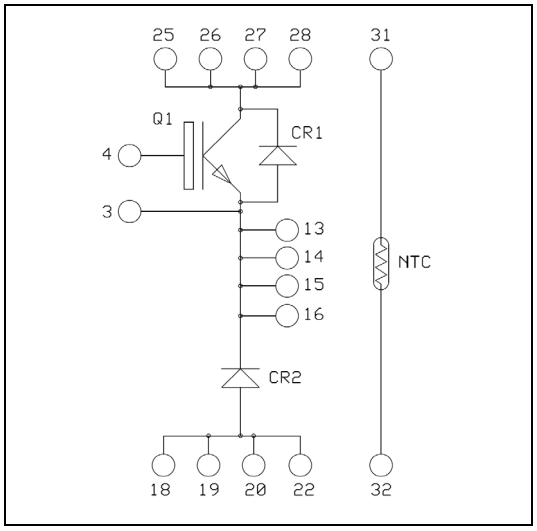
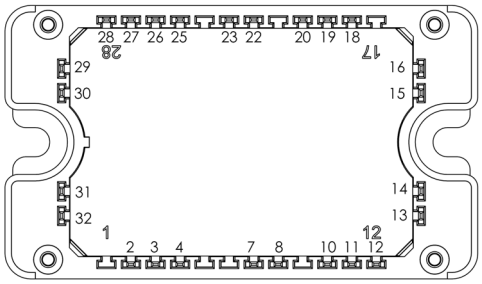
APTGTQ200SK65T3G

Buck chopper
High speed IGBT 5 Power Module

V_{CES} = 650V
I_C = 200A @ Tc = 25°C





Pins 25/26/27/28 ; 13/14/15/16 ; 18/19/20/22 must be shorted together

Application
- AC and DC motor control
- Switched Mode Power Supplies

Features
- High speed IGBT 5
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Low leakage current
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Voltage		650	V
I_C	Continuous Collector Current	T_C = 25°C	200	A
		T_C = 80°C	120	
I_{CM}	Pulsed Collector Current	T_C = 25°C	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation		483	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 650V				200	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V I_C = 200A	T_j = 25°C		1.65	2.2	V
			T_j = 150°C		1.9		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 2mA		3.3	4.0	4.7	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				480	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			12		nF
C_{oes}	Output Capacitance				0.2		
C_{res}	Reverse Transfer Capacitance				0.044		
Q_G	Gate charge	V_{GE} = 15V, I_C = 200A V_{CE} = 520V			480		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V V_{Bus} = 400V I_C = 100A R_G = 1Ω			21		ns
T_r	Rise Time				15		
$T_{d(off)}$	Turn-off Delay Time				180		
T_f	Fall Time				18		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = 15V V_{Bus} = 400V I_C = 100A R_G = 1Ω			20		ns
T_r	Rise Time				15		
$T_{d(off)}$	Turn-off Delay Time				205		
T_f	Fall Time				26		
E_{on}	Turn on Energy	V_{GE} = 15V V_{Bus} = 400V I_C = 100A R_G = 1Ω	T_j = 150°C		3		mJ
E_{off}	Turn off Energy		T_j = 150°C		1.2		
R_{Gint}	Integrated gate resistor				1.25		Ω
R_{thJC}	Junction to Case Thermal Resistance					0.31	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	V_R=650V				200	µA
I_F	DC Forward Current		Tc = 25°C		200		A
V_F	Diode Forward Voltage	I_F = 200A V_{GE} = 0V	T_j = 25°C		1.6	2.2	V
			T_j = 150°C		1.65		
t_{rr}	Reverse Recovery Time	I_F = 100A V_R = 400V di/dt =6000A/µs	T_j = 25°C		46		ns
			T_j = 150°C		62		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		2		µC
			T_j = 150°C		4		
R_{thJC}	Junction to Case Thermal Resistance					0.35	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

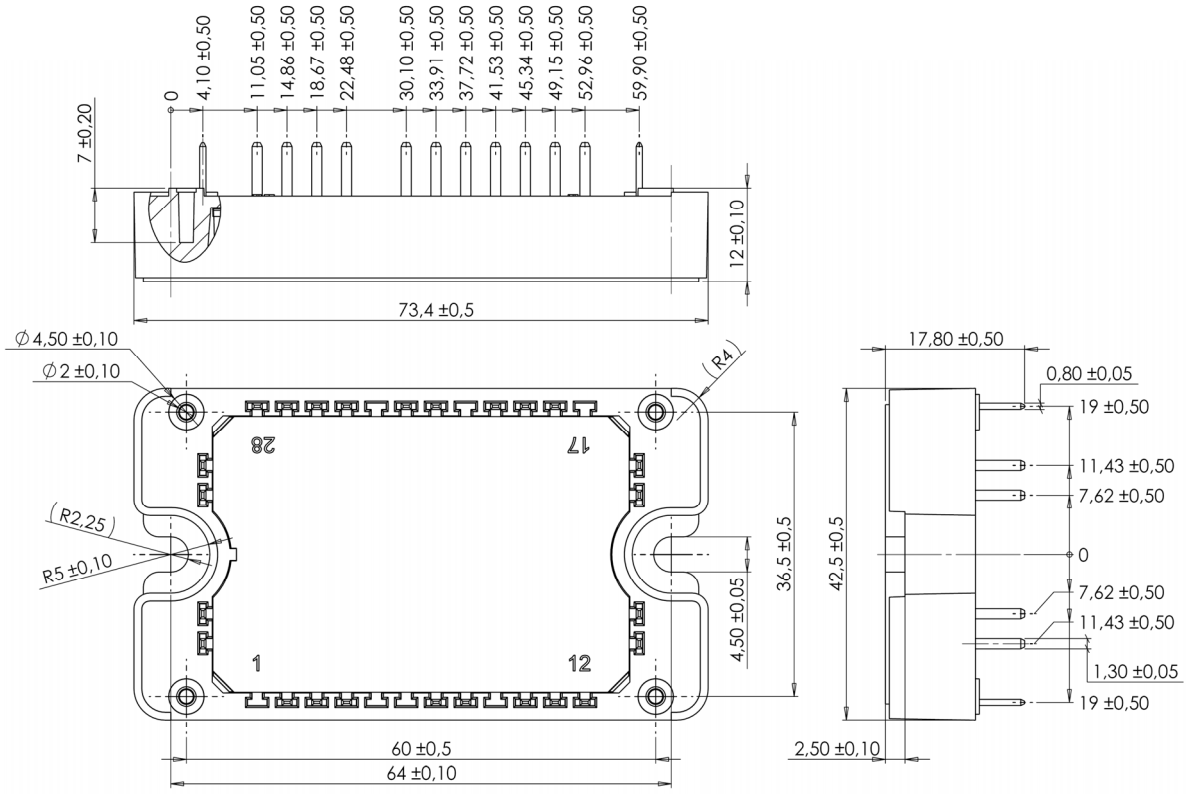
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

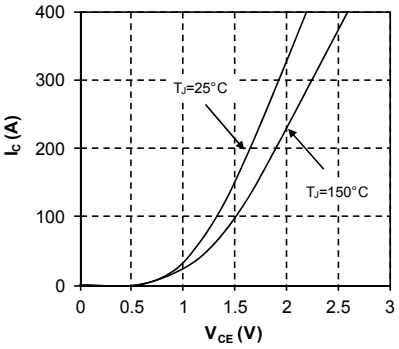
Package outline (dimensions in mm)



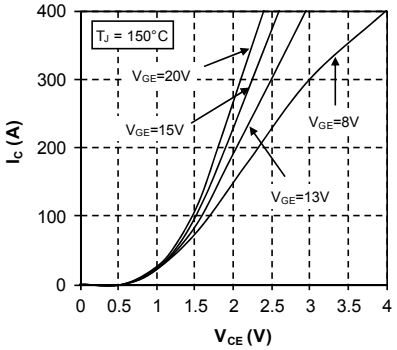
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical performance curve

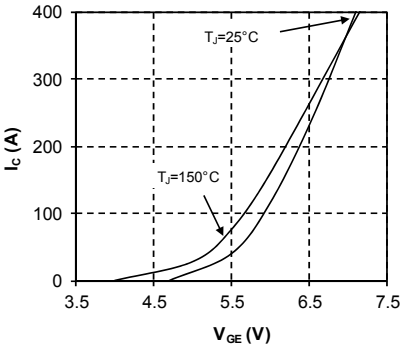
Output Characteristics (V_{GE}=15V)



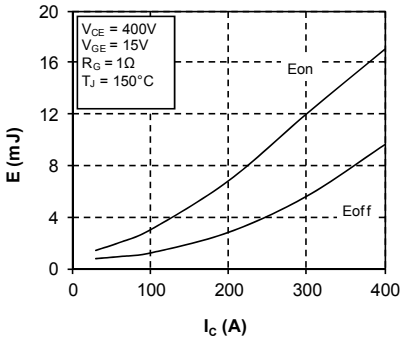
Output Characteristics



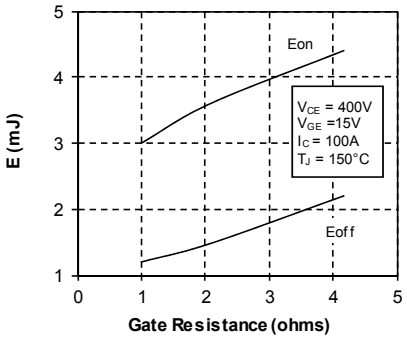
Transfert Characteristics



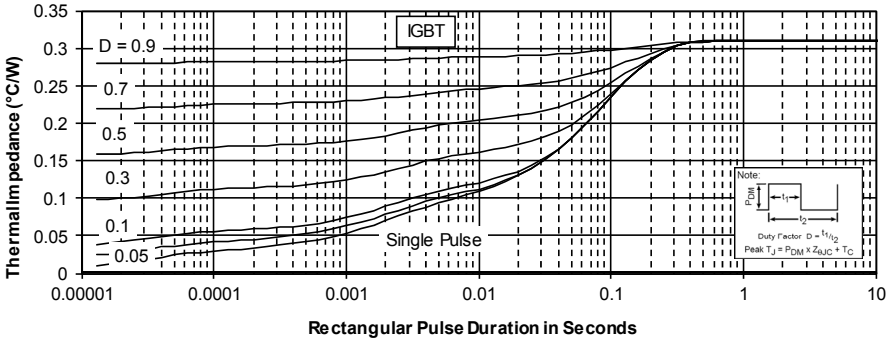
Energy losses vs Collector Current

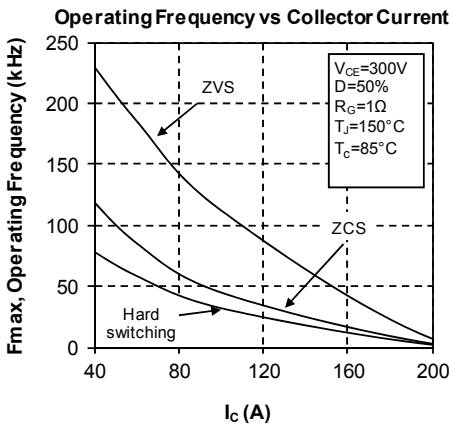


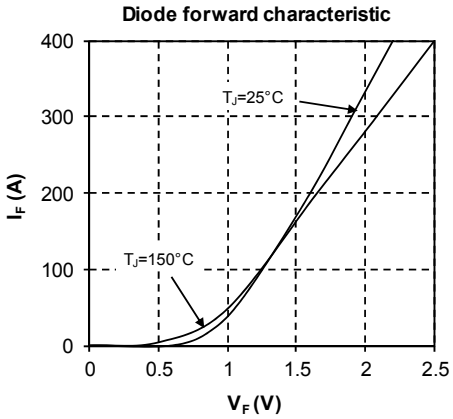
Switching Energy Losses vs Gate Resistance

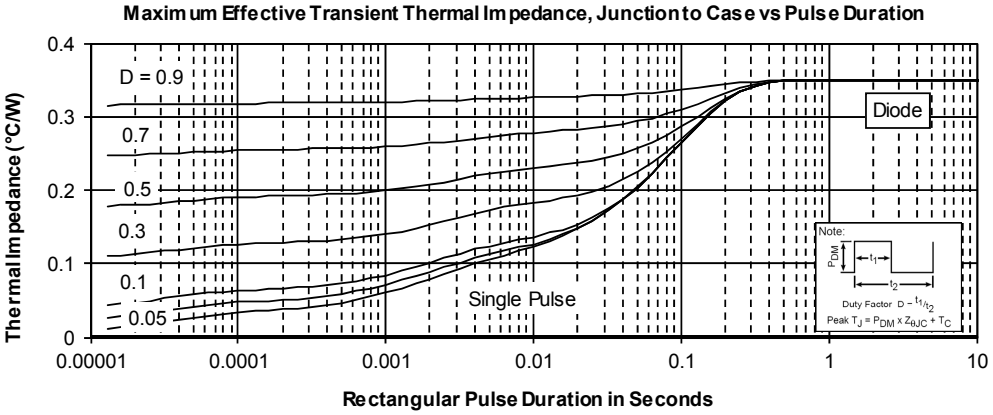


Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration




Operating Frequency vs Collector Current
Fmax, Operating Frequency (kHz)
250
200
150
100
50
0
40
80
120
160
200
I_C (A)
ZVS
ZCS
Hard switching
V_{CE}=300V
D=50%
R_G=1Ω
T_J=150°C
T_c=85°C


Diode forward characteristic
I_F (A)
400
300
200
100
0
0
0.5
1
1.5
2
2.5
V_F (V)
T_J=25°C
T_J=150°C


Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration
Thermal Impedance (°C/W)
0.4
0.3
0.2
0.1
0
0.00001
0.0001
0.001
0.01
0.1
1
10
Rectangular Pulse Duration in Seconds
D = 0.9
0.7
0.5
0.3
0.1
0.05
Single Pulse
Diode
Note:
Duty Factor D = t_1/t_2
Peak T_J = P_{DM} x $Z_{\theta JC}$ + T_C

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